

BACK-END

SiC/GaN Chip

MOS-FET

IGBT

DIODE

SWITCHING TIME TEST SYSTEM スイッチングタイムテストシステム

SWQS2050ZZ 2000V
5000A

NEW

- SWQS2050ZZ has been designed to test the short circuit tolerance and the switching characteristics of IGBT, MOS-FET, SiC/GaN chips, etc.
- SWQS2050ZZ は、IGBT、MOS-FET、SiC/GaN チップ等のスイッチング特性、及び短絡耐量を測定する装置です。



Note) The equipment of the left side in a picture (Temperature environmental system) is an option.
注) 写真左側の装置 (温度環境試験器) はオプション品です。

MODEL

SWQS2050ZZ

TEST ITEMS

L-LOAD/R-LOAD SWITCHING	lc(lD), td(on), tr, td(off), tf, e(on), e(off)
di/dt	Irr, trr, Qrr, dif/dt, dir/dt, Vdsurge
AVALANCHE	Iava, Vava, Eava, Vsurge
QG	t1, t2, t3, Qgs, Qgd, Qg, Vth
SHORT CIRCUIT ASO	Vsc, Isc, Vsurge, Esc

SETTING RANGE

MEASURABLE DEVICE	SiC/GaN Chip, IGBT, MOS-FET, DIODE
MEASUREMENT RANGE	000.0 μ s ~ 999.9 μ s
VDD	0020V ~ 2000V 1V STEP
ID (limit)	0001A ~ 5000A 1A STEP
VGP (VGF/VGR) /VGN (VGF/VGR)	\pm 00.00V ~ \pm 30.0V 0.01V STEP
IG	To choose from 0.1mA, 1mA and 10mA
Time-1	000.0 μ s ~ 9999.9 μ s 0.1 μ s STEP
Time-2	000.0 μ s ~ 999.9 μ s 0.1 μ s STEP
Time-3	000.0 μ s ~ 99.9 μ s 0.1 μ s STEP
Time-4	000.0 μ s ~ 9999 μ s 1 μ s STEP
GATE RESISTANCE (Rg)	Plug-in method
LOAD RESISTANCE	Plug-in method
LOAD COIL	Plug-in method

POWER AREA

L-LOAD/R-LOAD SWITCHING	2000V/1000A/200 μ s
di/dt	2000V/1000A/200 μ s
AVALANCHE	2000V/1000A/200 μ s
SHORT CIRCUIT ASO	2000V/5000A/100 μ s
QG	2000V/1000A/200 μ s

BINNING

OPEN/SHORT CHECK	Vg ON : VCE \geq 10V...OPEN Vg OFF : VCE \leq 1/2 VDD...SHORT
BIN INDICATION	ERROR, PASS, LIMIT-FAIL, OPEN, SHORT

DIMENSIONS & WEIGHT

MAIN UNIT	550(W) \times 860(D) \times 1700(H)...290kg (include oscilloscope)
MEASUREMENT UNIT	723(W) \times 1000(D) \times 2352(H)...385kg